N-Channel Enhancement Mode Field Effect Transistor

Product Summary

● V_{DS}	30V
● I_D	3.6A
● $R_{DS(ON)}$(at V_{GS}=10V)	33mohm
● $R_{DS(ON)}$(at V_{GS}=4.5V)	48mohm

● 100% V_{DS} Tested

General Description

- Trench Power MV MOSFET technology
- High Power and current handing capability
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- PWM application
- Load switch

■ Absolute Maximum Ratings (T$_A$=25 unless otherwise noted)

Parameter	Symbol	Limit	Unit

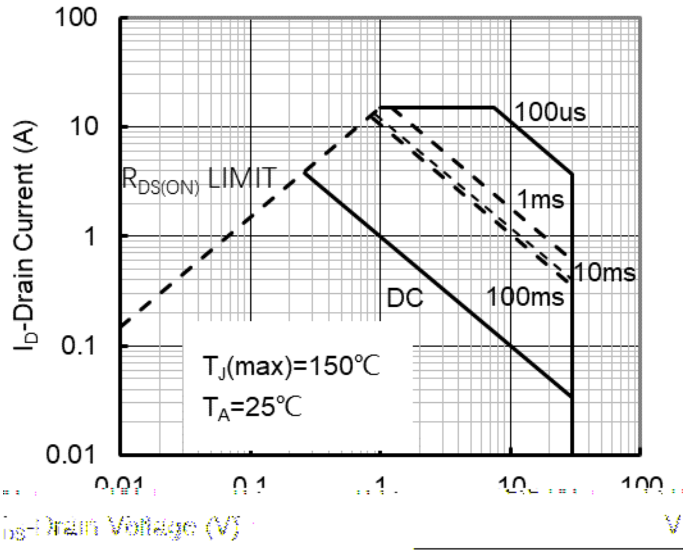


Figure7. Safe Operation Area

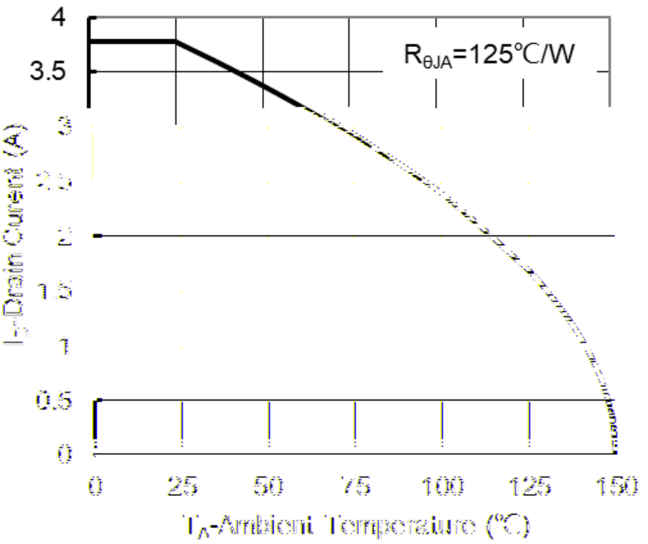


Figure8. Maximum Continuous Drain Current vs Ambient Temperature

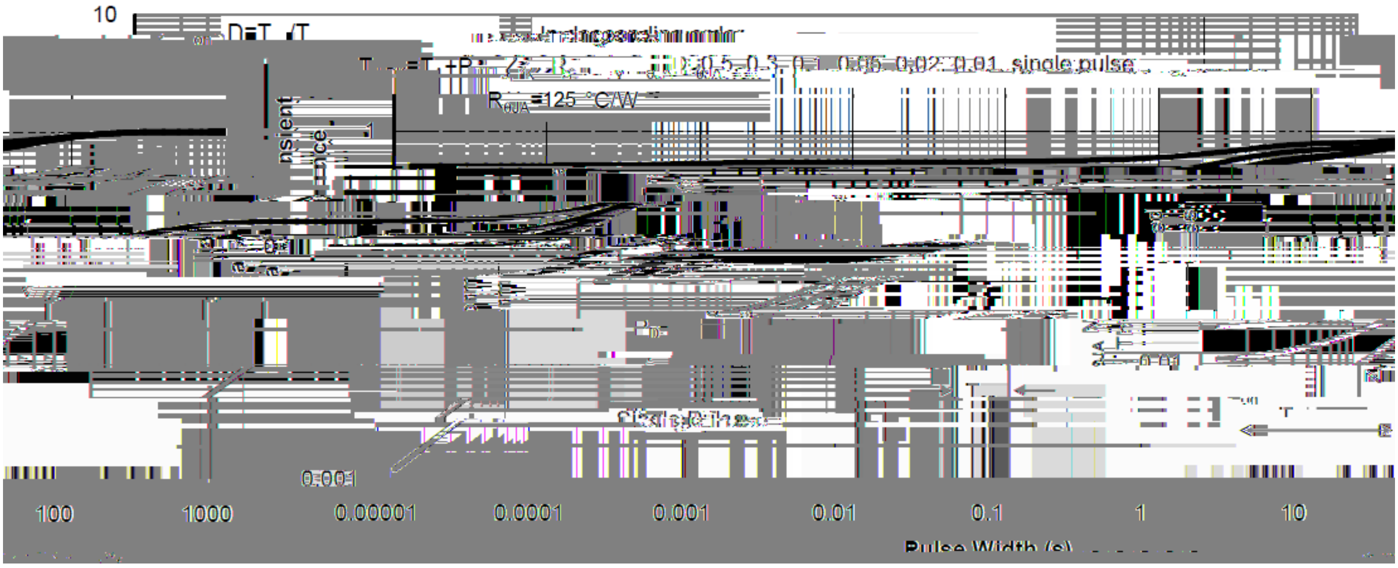
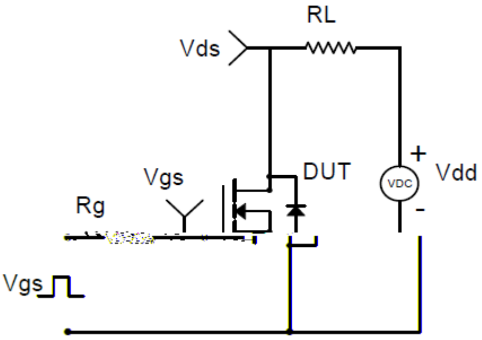
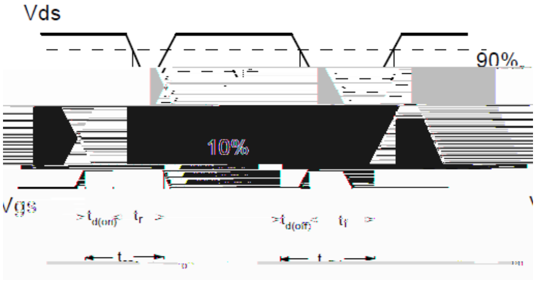


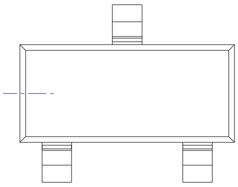
Figure9. Normalized Maximum Transient Thermal Impedance

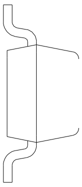


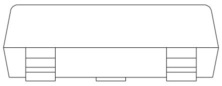
Resistive



■ SOT-23 Package information







UNIT mm

Disclaimer

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The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, tri5rnt r the96.04 842.04 rum/F5 9[m)-6(e)-3(d)-3(i)9(c)-6(h)-3(i)-4(g9(t)-4r)-15(d)-3(e)-,(d)-3(i)9(am)6(a)-3(n)-3(l)-4()11